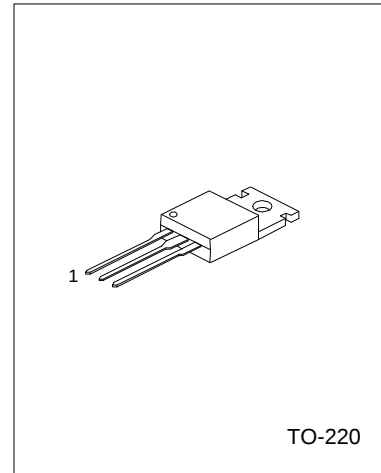


UTC D313 NPN EPITAXIAL PLANAR TRANSISTOR

NPN EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The UTC D313 is designed for use in general purpose amplifier and switching applications.



1:BASE 2:COLLECTOR 3:EMITTER

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	Ic	3	A
Storage Temperature	T _{STG}	-55 ~ +150	°C
Junction Temperature	Tj	150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BVCBO	IC=1mA	60			V
Collector-Emitter Breakdown Voltage	BVCEO	IC=10mA	60			V
Emitter-Base Breakdown Voltage	BVEBO	IE=100uA	5			V
Collector Cut-Off Current	ICBO	VCB=20V, IE=0			0.1	mA
Emitter Cut-Off Current	IEBO	VEB=4V, IC=0			1.0	mA
Collector-Emitter Saturation Voltage	VCE(SAT)	IC=2A, IB=0.2A			1.0	V
Base-Emitter On voltage	VBE(ON)	VCE=2V, IC=1A			1.5	V
DC Current Gain	hFE	IC=1A, VCE=2V	40		320	
		IC=0.1A, VCE=2V	40			

CLASSIFICATION ON hFE

RANK	C	D	E	F
RANGE	40-80	60-120	100-200	160-320

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